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FPF2G120BF07AS

F2, 3ch Boost module with NTC

General Description

The FPF2G120BF07AS is the 3ch boost topology which is providing an optimized solution for the multi-string solar application. And the integrated high speed field stop IGBTs and SiC diodes are providing lower conduction and switching losses. Furthermore, the screw clamp provides a fast and reliable mounting method.

Electrical Features

- High Efficiency
- Low Conduction and Switching Losses
- High Speed Field Stop IGBT
- SiC SBD for Boost Diode
- Built-in NTC for Temperature Monitoring

Mechanical Features

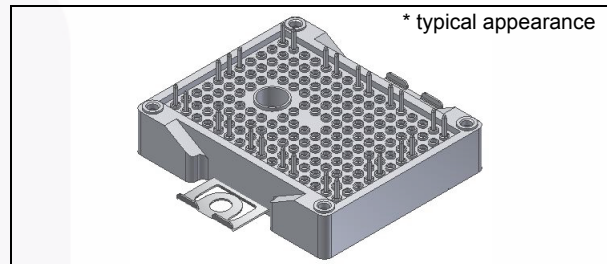
- Compact Size : F2 Package
- Soldering Pin
- Al₂O₃ Substrate with Low Thermal Resistance

Applications

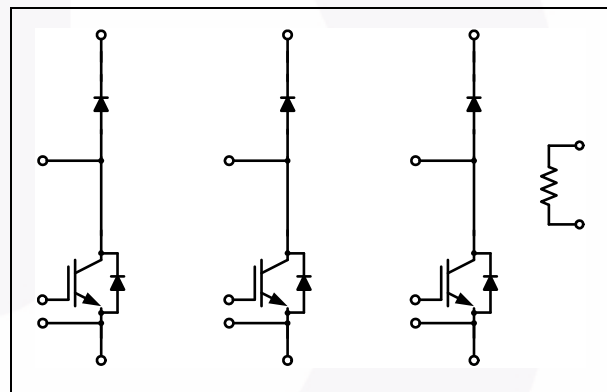
- Solar Inverter

Related Materials

- AN-5077: Design Considerations for High Power Module (HPM)



Package Code: F2



Internal Circuit Diagram

Package Marking and Ordering Information

Device	Device Marking	Package	PCM	Packing Type	Quantity / Tray
FPF2G120BF07AS	FPF2G120BF07AS	F2	X	Tray	14
FPF2G120BF07ASP	FPF2G120BF07ASP	F2	O	Tray	14

FPF2G120BF07AS - F2, 3ch Boost module with NTC

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Description	Condition	Rating	Units
Boost IGBT				
V_{CES}	Collector-Emitter Voltage		650	V
V_{GES}	Gate-Emitter Voltage		± 20	V
	Transient Gate-Emitter Voltage		± 25	V
I_C	Continuous Collector Current	$T_C = 80^\circ\text{C}$, $T_{Jmax} = 175^\circ\text{C}$	40	A
I_{CM}	Pulsed Collector Current	limited by T_{Jmax}	80	A
P_D	Maximum Power Dissipation		156	W
T_J	Operating Junction Temperature		- 40 to + 150	$^\circ\text{C}$
Protection Diode				
V_{RRM}	Peak Repetitive Reverse Voltage		650	V
I_F	Continuous Forward Current	$T_C = 80^\circ\text{C}$, $T_{Jmax} = 175^\circ\text{C}$	15	A
I_{FM}	Maximum Forward Current		30	A
I_{FSM}	Non-repetitive Peak Surge Current	60Hz Single Half-Sine Wave	150	A
I^2t - value	Surge Current Integral Value		93	A^2s
P_D	Maximum Power Dissipation		140	W
T_J	Operating Junction Temperature		- 40 to + 150	$^\circ\text{C}$
Boost Diode				
V_{RRM}	Peak Repetitive Reverse Voltage		650	V
I_F	Continuous Forward Current	$T_C = 80^\circ\text{C}$, $T_{Jmax} = 175^\circ\text{C}$	15	A
I_{FM}	Maximum Forward Current		30	A
I_{FSM}	Non-repetitive Peak Surge Current	60Hz Single Half-Sine Wave	120	A
I^2t - value	Surge Current Integral Value		60	A^2s
P_D	Maximum Power Dissipation		98	W
T_J	Operating Junction Temperature		- 40 to + 150	$^\circ\text{C}$
Module				
T_{STG}	Storage Temperature		- 40 to + 125	$^\circ\text{C}$
V_{ISO}	Isolation Voltage	AC 1 min.	2500	V
Iso_Material	Internal Isolation Material		Al_2O_3	-
T_{MOUNT}	Mounting Torque		2.0 to 5.0	N•m
Creepage	Terminal to Heat Sink		11.5	mm
	Terminal to Terminal		6.3	mm
Clearance	Terminal to Heat Sink		10.0	mm
	Terminal to Terminal		5.0	mm

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units	
Boost IGBT							
Off Characteristics							
BV_{CES}	Collector-Emitter Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$	650	-	-	V	
I_{CES}	Collector Cut-off Current	$V_{CE} = V_{CES}, V_{GE} = 0\text{ V}$	-	-	250	μA	
I_{GES}	Gate-Emitter Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0\text{ V}$	-	-	± 2	μA	
On Characteristics							
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$V_{GE} = V_{CE}, I_C = 40\text{ mA}$	3.9	5.1	6.8	V	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 40\text{ A}, V_{GE} = 15\text{ V}$	-	1.55	2.2	V	
		$I_C = 40\text{ A}, V_{GE} = 15\text{ V}, T_C = 125^\circ\text{C}$	-	1.85	-	V	
R_{LEAD}	Lead Resistance of Pin to Chip	per Chip	-	3.3	-	$\text{m}\Omega$	
Switching Characteristics							
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 300\text{ V}$ $I_C = 40\text{ A}$ $V_{GE} = 15\text{ V}$ $R_G = 15\ \Omega$ Inductive Load $T_C = 25^\circ\text{C}$	-	24	-	ns	
t_r	Rise Time		-	24	-	ns	
$t_{d(off)}$	Turn-Off Delay Time		-	132	-	ns	
t_f	Fall Time		-	17	-	ns	
E_{ON}	Turn-On Switching Loss per Pulse		-	0.40	-	mJ	
E_{OFF}	Turn-Off Switching Loss per Pulse		-	0.28	-	mJ	
$t_{d(on)}$	Turn-On Delay Time		$V_{CC} = 300\text{ V}$ $I_C = 40\text{ A}$ $V_{GE} = 15\text{ V}$ $R_G = 15\ \Omega$ Inductive Load $T_C = 125^\circ\text{C}$	-	22	-	ns
t_r	Rise Time			-	27	-	ns
$t_{d(off)}$	Turn-Off Delay Time			-	148	-	ns
t_f	Fall Time			-	17	-	ns
E_{ON}	Turn-On Switching Loss per Pulse	-		0.59	-	mJ	
E_{OFF}	Turn-Off Switching Loss per Pulse	-		0.37	-	mJ	
Q_g	Total Gate Charge	$V_{CC} = 300\text{ V}, I_C = 40\text{ A}, V_{GE} = 15\text{ V}$		-	65	-	nC
$R_{\theta JC}$	Thermal Resistance of Junction to Case	per Chip	-	-	0.96	$^\circ\text{C}/\text{W}$	
Protection Diode							
V_F	Diode Forward Voltage	$I_F = 15\text{ A}$	-	1.05	1.4	V	
		$I_F = 15\text{ A}, T_C = 125^\circ\text{C}$	-	0.95	-	V	
R_{LEAD}	Lead Resistance of Pin to Chip	per Chip	-	2.4	-	$\text{m}\Omega$	
I_R	Reverse Leakage Current	$V_R = 650\text{ V}$	-	-	250	μA	
$R_{\theta JC}$	Thermal Resistance of Junction to Case	per Chip	-	-	1.07	$^\circ\text{C}/\text{W}$	
Boost Diode							
V_F	Diode Forward Voltage	$I_F = 15\text{ A}$	-	1.45	1.9	V	
		$I_F = 15\text{ A}, T_C = 125^\circ\text{C}$	-	1.75	-	V	
R_{LEAD}	Lead Resistance of Pin to Chip	per Chip	-	2.8	-	$\text{m}\Omega$	
I_R	Reverse Leakage Current	$V_R = 650\text{ V}$	-	-	60	μA	
I_{rr}	Reverse Recovery Current	$V_R = 300\text{ V}, I_F = 15\text{ A},$ $di / dt = 1390\text{ A}/\mu\text{s},$ $T_C = 25^\circ\text{C}$	-	9.2	-	A	
Q_C	Total Capacitive Charge	$T_C = 125^\circ\text{C}$	-	60	-	nC	
E_{rec}	Reverse Recovery Energy		-	4.9	-	μJ	
I_{rr}	Reverse Recovery Current		$V_R = 300\text{ V}, I_F = 15\text{ A},$ $di / dt = 1390\text{ A}/\mu\text{s},$ $T_C = 125^\circ\text{C}$	-	9.2	-	A
Q_C	Total Capacitive Charge	$T_C = 125^\circ\text{C}$	-	65	-	nC	
E_{rec}	Reverse Recovery Energy		-	4.9	-	μJ	
$R_{\theta JC}$	Thermal Resistance of Junction to Case	per Chip	-	-	1.52	$^\circ\text{C}/\text{W}$	

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
NTC(Thermistor)						
R_{NTC}	Rated Resistance	$T_C = 25^\circ\text{C}$	-	10	-	$k\Omega$
		$T_C = 100^\circ\text{C}$	-	936	-	Ω
	Tolerance	$T_C = 25^\circ\text{C}$	-3	-	+3	%
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	-	-	20	mW
B_{Value}	B-Constant	$B_{25/50}$	-	3450	-	K
		$B_{25/100}$	-	3513	-	K

Typical Performance Characteristics

Fig 1. Typical Output Characteristics - IGBT

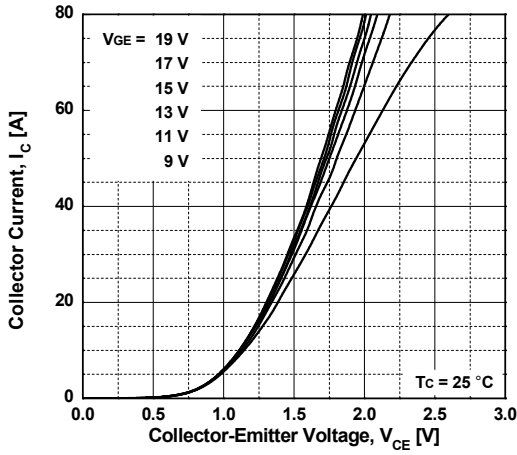


Fig 2. Typical Output Characteristics - IGBT

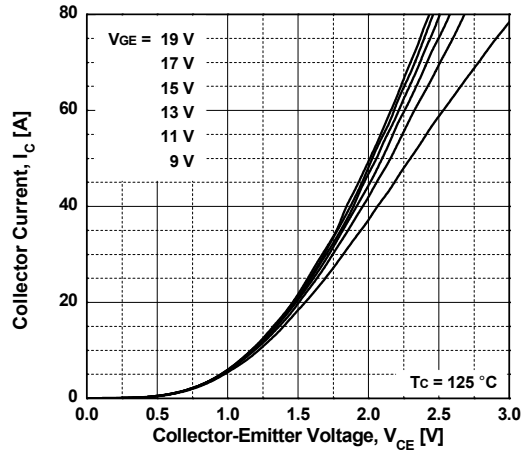


Fig 3. Typical Saturation Voltage Characteristics - IGBT

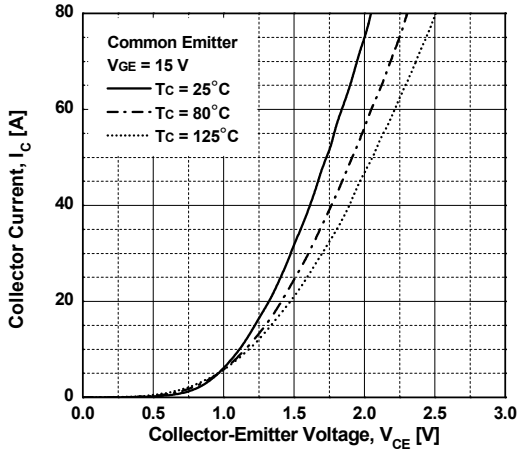


Fig 4. Switching Loss vs. Collector Current - IGBT

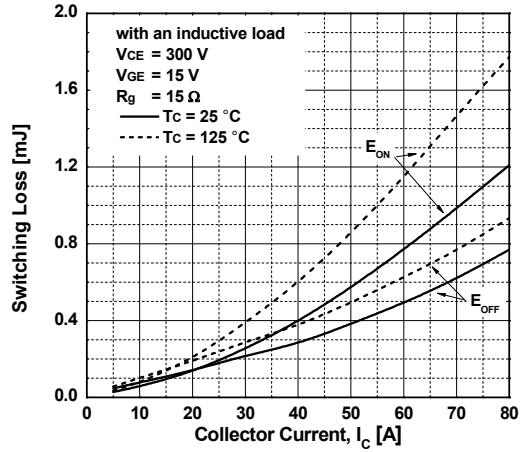


Fig 5. Switching Loss vs. Gate Resistance - IGBT

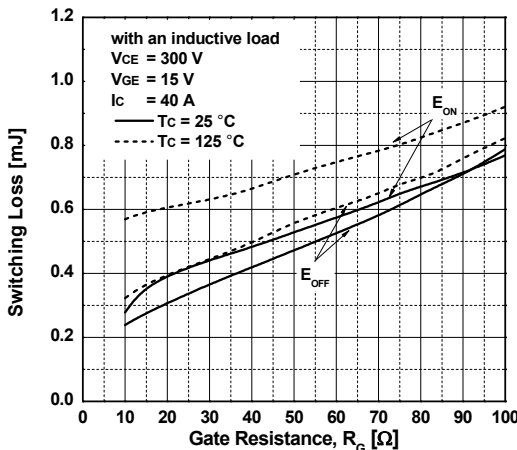
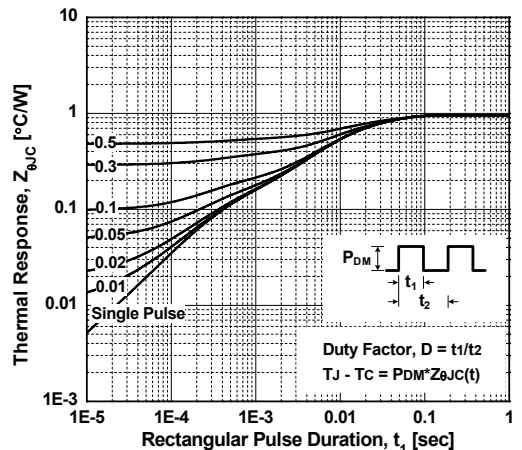


Fig 6. Transient Thermal Impedance - IGBT



Typical Performance Characteristic

Fig 7. Typical Forward Voltage Drop - Protection Diode

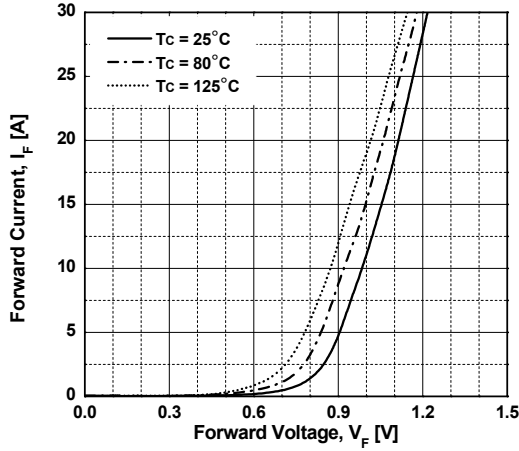


Fig 8. Transient Thermal Impedance - Protection Diode

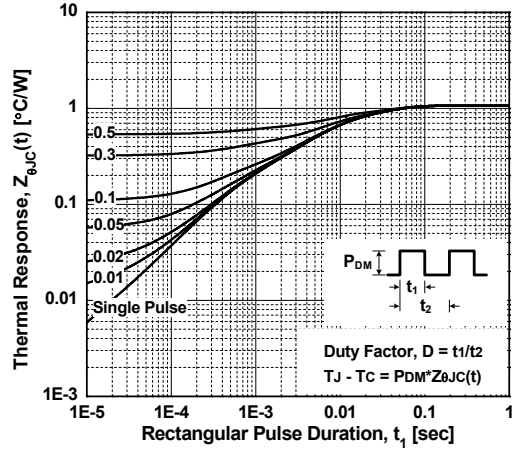


Fig 9. Typical Forward Voltage Drop - Boost Diode

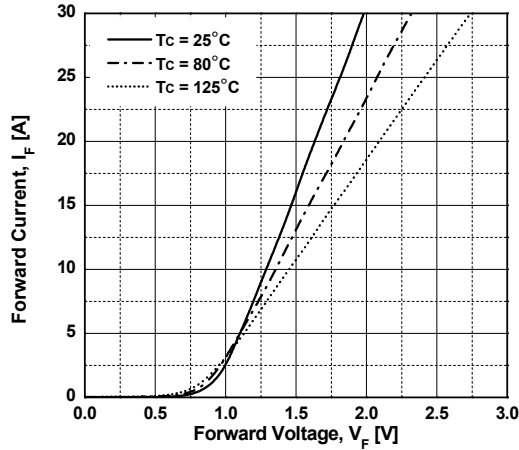


Fig 10. Reverse Recovery Energy vs. Forward Current - Boost Diode

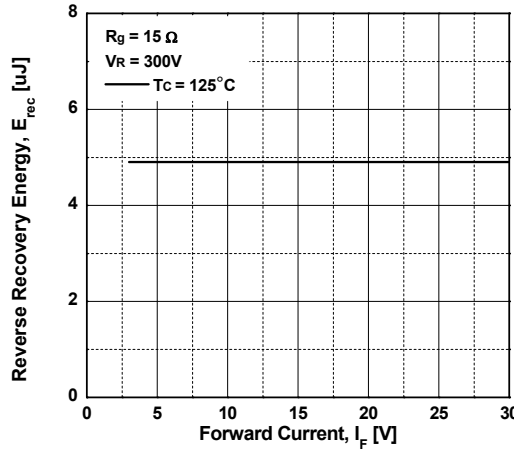


Fig 11. Reverse Recovery Energy vs. Gate Resistance - Boost Diode

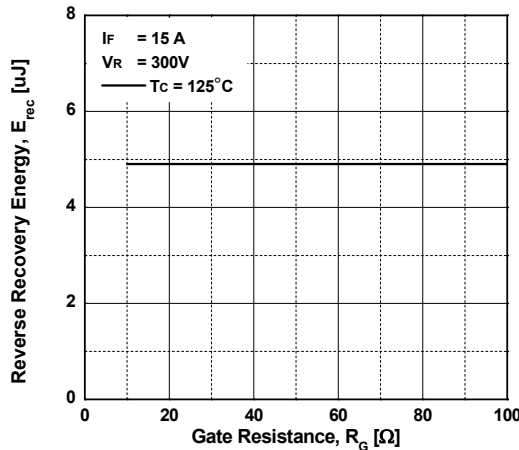
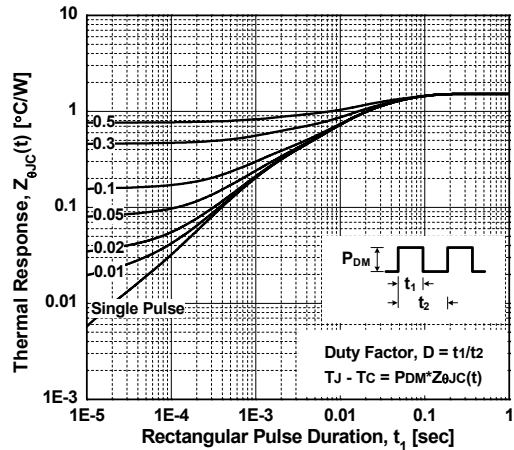
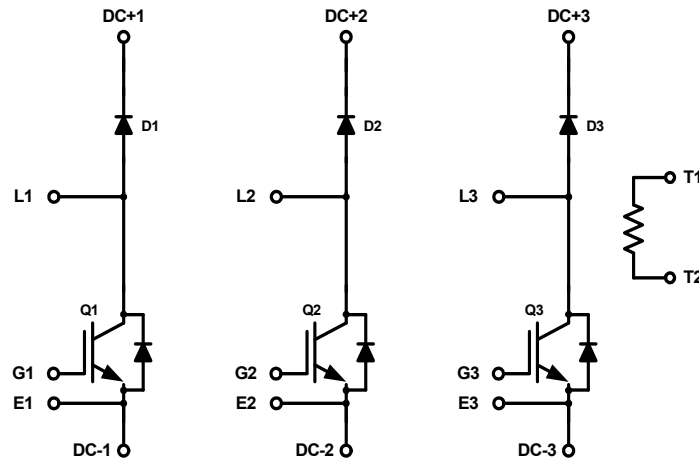


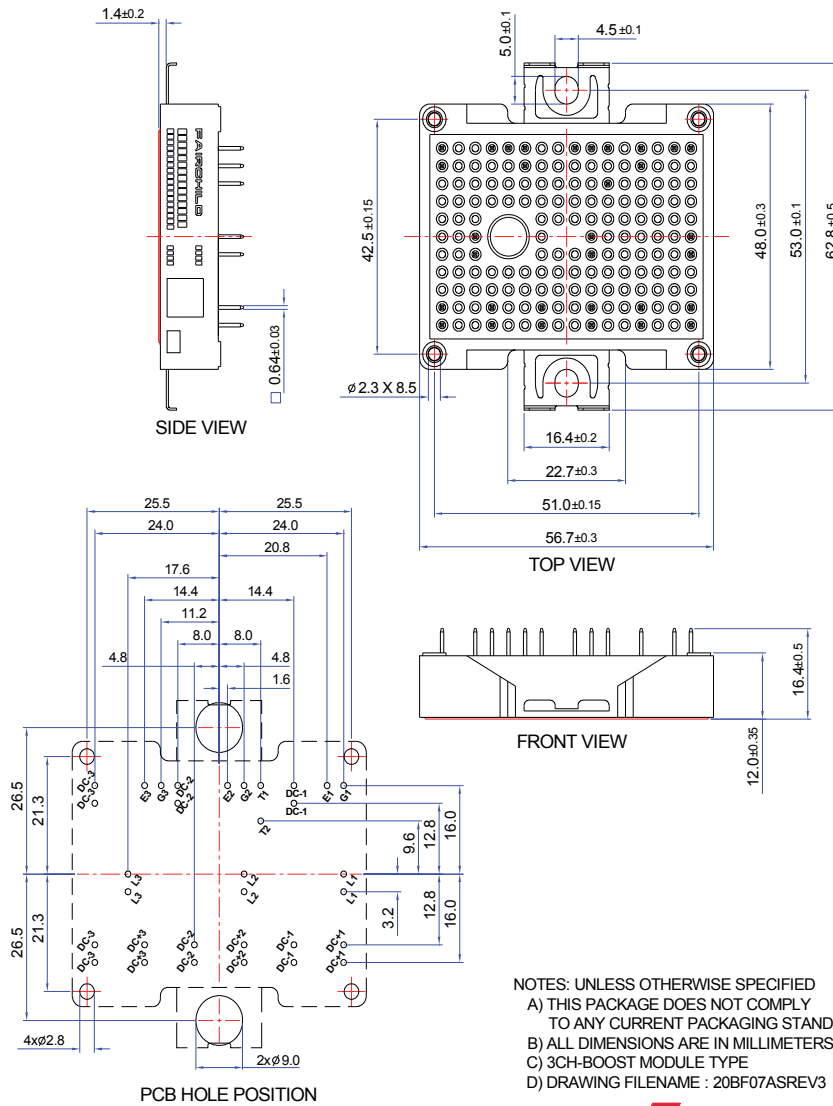
Fig 12. Transient Thermal Impedance - Boost Diode



Internal Circuit Diagram



Package Outlines [mm]



NOTES: UNLESS OTHERWISE SPECIFIED
 A) THIS PACKAGE DOES NOT COMPLY TO ANY CURRENT PACKAGING STANDARD
 B) ALL DIMENSIONS ARE IN MILLIMETERS
 C) 3CH-BOOST MODULE TYPE
 D) DRAWING FILENAME : 20BF07ASREV3

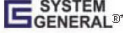




- PIN-GRID 3.2mm
 - TOLERANCE OF PCB HOLE PATTERN $\pm \varnothing 0.1$





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No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
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